

# SPICE Device Model Si7326DN

### **Vishay Siliconix**

### N-Channel 30-V (D-S) Fast Switching MOSFET

#### **CHARACTERISTICS**

- N-Channel Vertical DMOS
- Macro Model (Subcircuit Model)
- Level 3 MOS

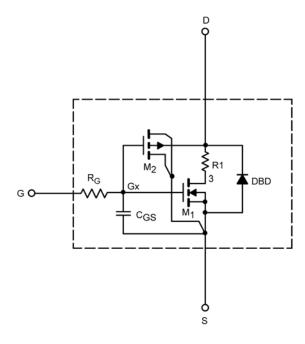
- · Apply for both Linear and Switching Application
- Accurate over the -55 to 125°C Temperature Range
- Model the Gate Charge, Transient, and Diode Reverse Recovery Characteristics

#### **DESCRIPTION**

The attached spice model describes the typical electrical characteristics of the n-channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 to  $125^{\circ}$ C temperature ranges under the pulsed 0-V to 10-V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched  $C_{\rm gd}$  model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

#### SUBCIRCUIT MODEL SCHEMATIC



This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

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SPECIFICATIONS (T <sub>J</sub> = 25°C UNLESS OTHERWISE NOTED)					
Parameter	Symbol	Test Condition	Simulated Data	Measured Data	Unit
Static			<del>_</del>		•
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	1		V
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	281		Α
Drain-Source On-State Resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A	0.015	0.015	Ω
		$V_{GS}$ = 4.5 V, $I_{D}$ = 8 A	0.023	0.022	
Forward Transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A	20	16	S
Forward Voltage <sup>a</sup>	$V_{SD}$	$I_{\rm S}$ = 2.9 A, $V_{\rm GS}$ = 0 V	0.81	0.75	V
Dynamic <sup>b</sup>					•
Total Gate Charge	$Q_g$	V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 5 V, I <sub>D</sub> = 10 A	8.1	8.7	nC
Gate-Source Charge	$Q_{gs}$		1.5	1.5	
Gate-Drain Charge	$Q_{gd}$		3.5	3.5	

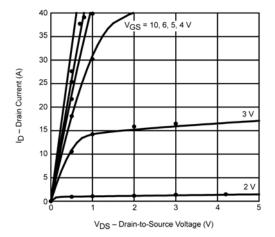
#### Notes

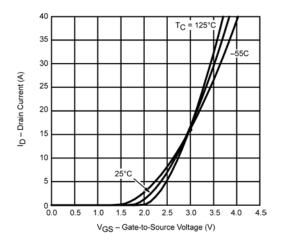
- a. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2%. b. Guaranteed by design, not subject to production testing.

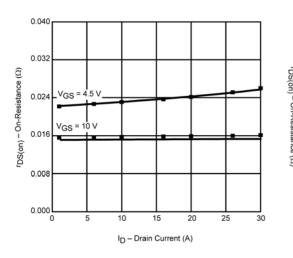


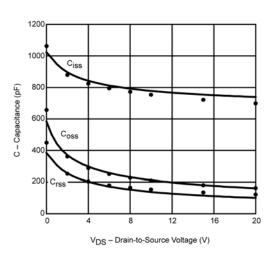
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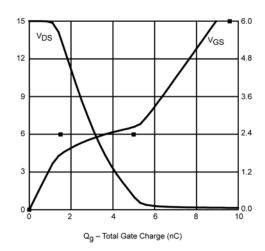
#### COMPARISON OF MODEL WITH MEASURED DATA (TJ=25°C UNLESS OTHERWISE NOTED)

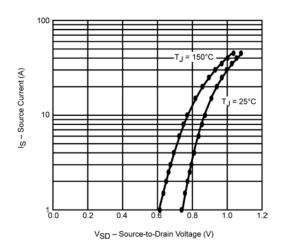












Note: Dots and squares represent measured data.



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